TOSHIBA Photocoupler GaAlAs Ired & Photo-IC

TLP557

Transistor Inverter
Inverter For Air Conditioner
Power Transistor Base Drive

The TOSHIBA TLP557 consists of a GaAlAs light emitting diode and an integrated photodetector.

This unit is 8-lead DIP package.

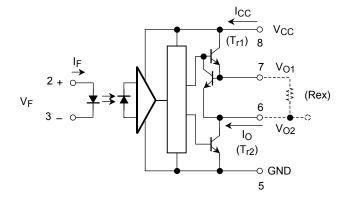
TLP557 is suitable for base driving circuit of power transistor module up to $20\mathrm{A}.$

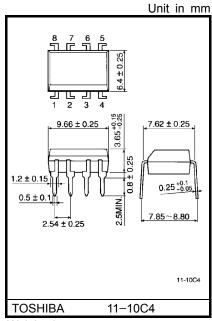
External resistor needs to connect between pin 6 and pin 7.

This is for constant current driving.

- Input threshold current: IF=5mA(max.)
- Guaranteed performance temperature range: -30~70°C
- Supply voltage: 16V(max.)
- Output current: ±0.3A(max.)
- Switching time (t_{pLH} / t_{pHL}): 5µs(max.)
- Isolation voltage: 2500V_{rms}(min.)
- UL recognized: UL1577, file No. E67349

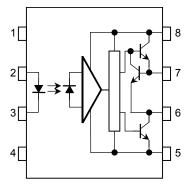
Schematic





Weight: 0.54g

Pin Configuration (top view)



- 1 : N.C.
- 2 : Anode
- 3 : Cathode
- 4 : N.C.
- 5: GND
- 6 : V_{O2}(Output)
- 7 : V_{O1}(Rex Terminal)
- 8 : V_{CC}

Truth Table

		Tr1	Tr2
Input	On	On	Off
LED	Off	Off	On

Absolute Maximum Ratings

	Characteristic		Symbol	Rating	Unit
	Forward current		I _F	25	mA
ED.	Peak transient forward current	(Note 1)	I _{FPT}	1	А
_	Reverse voltage		V _R	5	V
	Junction temperature		(T _j)	125	°C
	Output current (f ≤ 5kHz, Duty ≤ 50%)		IO	+0.32 / -0.32	А
	Peak output current (P _W ≤ 10µs, f ≤ 5kHz)		I _{OP}	+2 / -0.5	А
	Output voltage		Vo	16	V
ctor	Supply voltage		V _{CC}	16	V
Detector	O ₁ terminal to O ₂ terminal (pin 7–pin 6) voltage		V ₁ -2	1.5	V
	O ₂ terminal to O ₁ terminal (pin 6–pin 7) voltage		V ₂ -1	5	V
	Power dissipation	(Note 2)	Ро	0.5	W
	Junction temperature		(T _j)	125	°C
Total package power dissipation (Note 3)		Рот	0.55	W	
Operating temperature range		T _{opr}	-30~70	°C	
Storage temperature range		T _{stg}	-55~125	°C	
Lead solder temperature (10 s)		T _{sol}	260	°C	
Isolation voltage (AC, 1 min., R.H.≤ 60%, Ta=25°C) (Note 4)		BVS	BV _S 2500		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Pulse width PW ≤ 1µs, 300pps

(Note 2) $\Delta P_0 / ^{\circ}C = -6.7 \text{mW} / ^{\circ}C$ (Ta $\geq 50 ^{\circ}C$)

(Note 3) $\Delta P_{OT} / ^{\circ}C = -7.4 \text{mW} / ^{\circ}C \text{ (Ta } \ge 50 ^{\circ}C)$

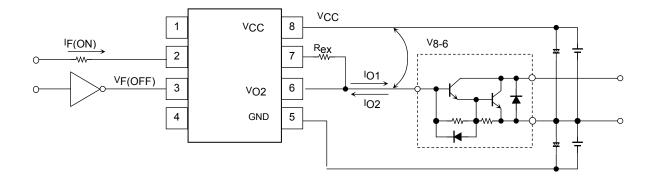
(Note 4) Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

Recommended Operating Condition

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Input current on	I _F (ON)	7	8	20	mA
Input voltage off	V _F (OFF)	0	_	0.8	V
Supply voltage	V _{CC}	5	6	13	V
I _{B1} Drive current	I ₀₁	_	0.15	0.25	Α
I _{B2} Drive current	I _{O2}	_	_	0.5	Α
External resistance	Rex	2.7	4.3	_	Ω
V _{CC} -V _{O2} (pin 8-pin 6) ON voltage	V ₈₋₆	2.3	3 (I _{O1} = 0.15A)	2.5 (I _{O1} = 0.25A)	V
Operating temperature	Topr	-30	25	70	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

(Rex is for constant current driving)



Electrical Characteristics (Ta = $-30\sim70$ °C, unless otherwise specified)

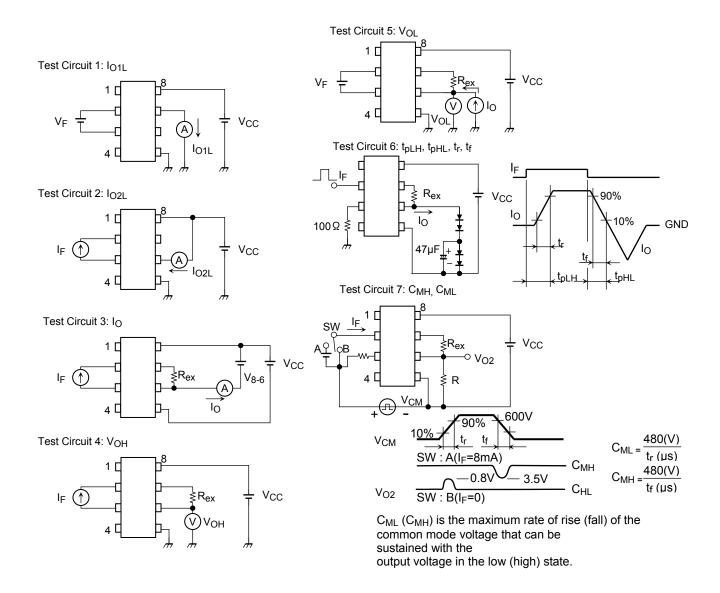
Characteristic	Symbol	Test Condition		Min.	Тур.*	Max.	Unit	Test Cir– cuit
Input forward voltage	V _F	I _F = 5mA , Ta = 25°C		_	1.55	1.7	V	
Temperature coefficient of forward voltage	ΔV _F / ΔTa	I _F = 5mA		_	-2.0	_	mV / °C	
Input reverse current	I _R	V _R = 5V, Ta = 25°C		_	ı	10	μA	
Input capacitance	C _T	V = 0 , f = 1MHz , Ta =	25°C		I	250	pF	
O ₁ Output leakage current	I _{O1L}	$V_{CC} = 16V, V_{O1} = 0, V_{F}$	= = 0.8V	_	0.01	200	μΑ	1
O ₂ Output leakage current	I _{O2L}	V _{CC} = 16V, V _{O2} = 16V, I _F = 5mA		_	0.2	200	μA	2
O Outrout surrount		V ₈₋₆ = 2.3V	V _{CC} = 6V	0.22	0.27	0.32	_	3
O ₁ Output current	lo	Rex = 2.7Ω I _F = 5mA, Ta = 25° C	V _{CC} = 16V	0.22	0.27	0.32	A	3
O ₂ High level output voltage	V _{OH}	V_{CC} = 6V, Rex = 2.7 Ω I _F = 5mA		3.5	5.5	_	٧	4
		$V_F = 0.8V$, Rex = 2.7 Ω $I_O = 0.25A$, Ta = 25°C	V _{CC} = 6V	_	0.2	0.4	V	
O ₂ Low level output	.,		V _{CC} = 16V	_	0.2	0.4	V	_
voltage	V _{OL}	V _F = 0.8V, Rex = 2.7Ω I _O = 0.5A (*1) Ta = 25°C	V _{CC} = 6V	_	0.4	_	V	5
			V _{CC} = 16V	_	0.4	_		
	Іссн	$V_{CC} = 6V, I_F = 5mA$ Rex = 2.7 Ω , Ta = 25°C		_	3.8	10	mA	
High level supply current		$V_{CC} = 6V$, $I_F = 5mA$, $Rex = 2.7\Omega$		_	-	13		
		V_{CC} = 16V, I_F = 5mA, Rex = 2.7 Ω		_	5.2	17		
	ICCL	$V_{CC} = 6V, I_F = 0mA$ Rex = 2.7 Ω , Ta = 25°C		_	11	17	mA	
Low level supply current		$V_{CC} = 6V$, $I_F = 0mA$, $Rex = 2.7\Omega$		_	_	22		
		V_{CC} = 16V, I_F = 0mA, Rex = 2.7 Ω		_	13	25		
"Output L→H" threshold	l _{FLH}	Rex = 2.7Ω I _O = $0.25A$ V _{O2} > $3V$	V _{CC} = 6V	_	2.5	5	mA	
input current			V _{CC} = 16V	_	_	5		
"Output H→L" threshold input current	V _{FHL}	Rex = 2.7Ω	V _{CC} = 6V	0.8	-	_	V	
		I _O = 0.25A V _{O2} < 0.4V	V _{CC} = 16V	0.8		_		
Input current hysterisis	I _{HYS}	V _{CC} = 6V, Rex = 2.7Ω, Ta = 25°C		_	0.05	_	mA	
Supply voltage	V _{CC}			5	-	16	V	
Capacitance (input-output)	CS	V _S = 0, f = 1MHz, Ta = 25°C		_	1.0	2.0	pF	
Resistance (input-output)	R _S	V _S = 500V , Ta = 25°C, R.H.≤ 60%		5×10 ¹⁰	10 ¹²	_	Ω	

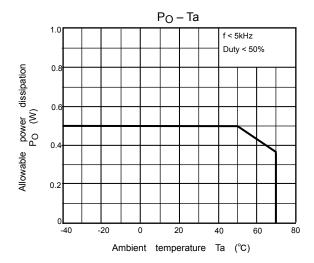
^{*} All typical values are at Ta = 25°C $\,$ (*1): Duration of I_O time \leq 100 μs

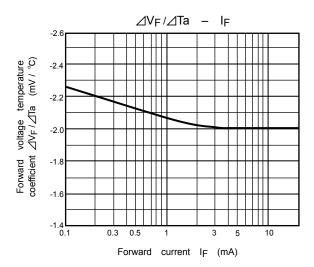
Switching Characteristics (Ta = $-30\sim70$ °C unless otherwise specified)

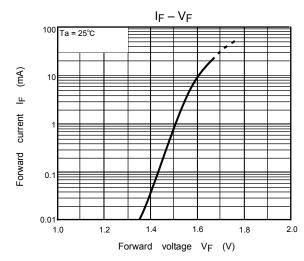
Characteristic	Symbol	Test Condition	Min.	Typ.*	Max.	Unit	Test Cir– cuit
Propagation delay time, L→H	tpLH		_	1	5	μs	
Propagation delay time, H→L	tpHL	$V_{CC} = 6V, I_F = 8mA$ Rex = 2.70	_	1	5	μs	6
Output rise time	t _r	f = 5kHz, Duty = 10%	_	0.05	_	μs	O
Output fall time	t _f		_	0.05	_	μs	
Common mode transient immunity at high level output	Смн	V_{CM} = 600V, I_F = 8mA V_{CC} = 6V, Rex = 270 Ω R = 1k Ω , Ta = 25°C	-2000	_	_	V / µs	7
Common mode transient immunity at low level output	C _{ML}	V_{CM} = 600V, I_F = 0mA V_{CC} = 6V, Rex = 270 Ω R = 1k Ω , Ta = 25°C	2000	_	_	V / µs	7

^{*} All typical values are at Ta = 25°C.









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